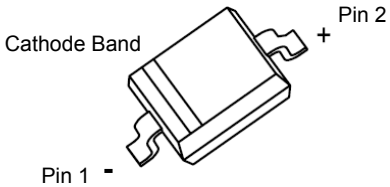
GOOD-ARK
SEMICONDUCTOR

GSD101AWS
Schottky Diode

Features

- Low forward voltage drop
- Guard ring construction for transient protection
- Negligible reverse recovery time
- Low reverse capacitance



SOD-323

Schematic Diagram

Absolute Maximum Ratings

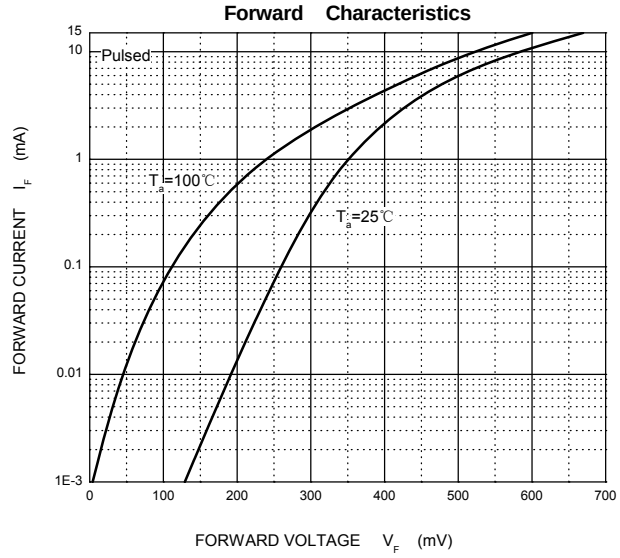
(T_A=25°C unless otherwise noted)

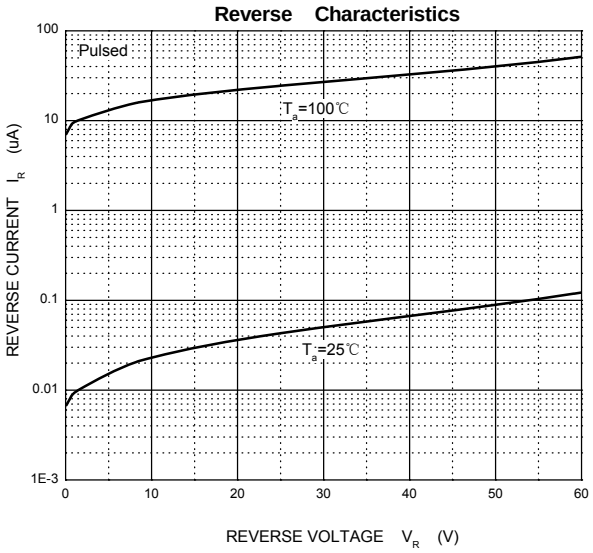
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	60	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS reverse Voltage	$V_{R(RMS)}$	42	V
Forward Continuous Current	I_{FM}	15	mA
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2	A
Power Dissipation	P_D	200	mW
Thermal Resistance from Junction to Ambient	$R_{\Theta JA}$	500	℃/W
Junction Temperature	T_j	125	℃
Storage Temperature	T_{STG}	-50 to +150	℃

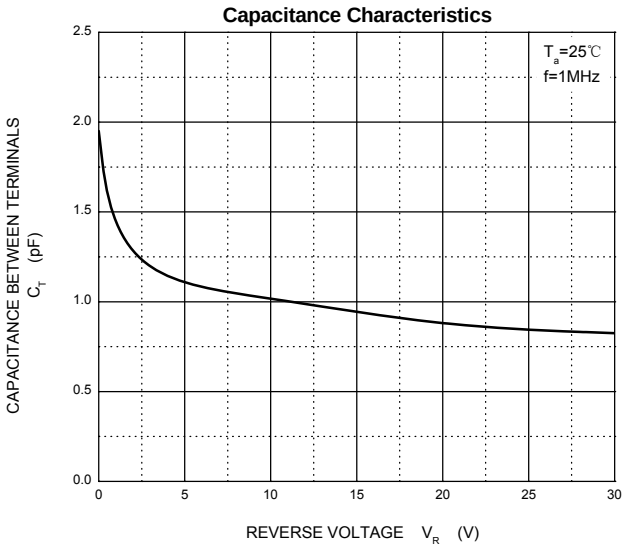
Electrical Characteristics (T_A=25°C unless otherwise noted)

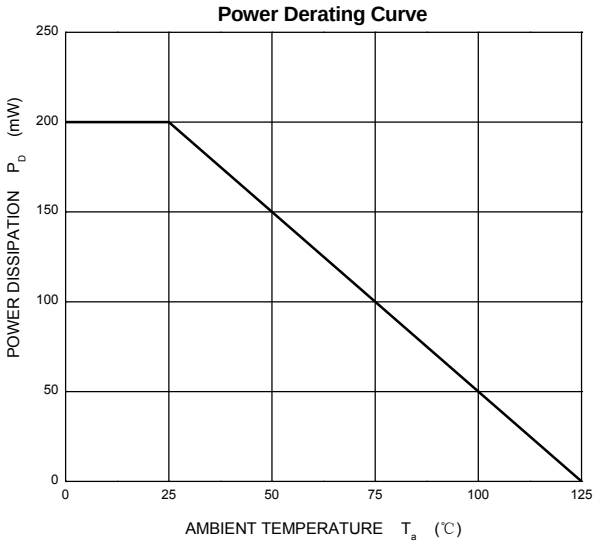
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse Voltage	$V_{(BR)}$	I_R=10μA	60	-	V
Reverse Current	I_R	V_R=50V	-	0.2	μA
Forward Voltage	V_F	I_F=1mA	-	0.41	V
		I_F=15mA	-	1	
Total Capacitance	C_{tot}	V_R=0V,f=1MHz	-	2	pF
Reverse Recovery Time	t_{rr}	I_F= I_R=5mA, I_{rr}=0.1×I_R, R_L=100Ω	-	1	ns

Typical Characteristic Curves

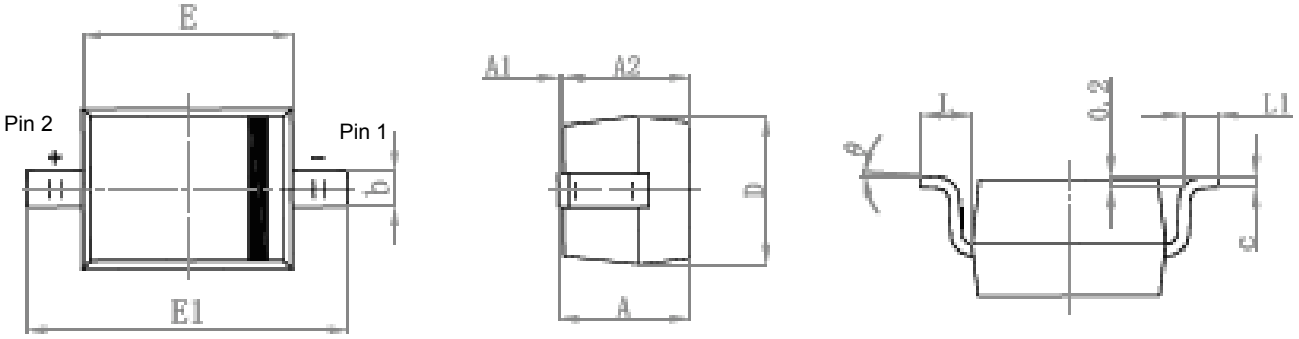








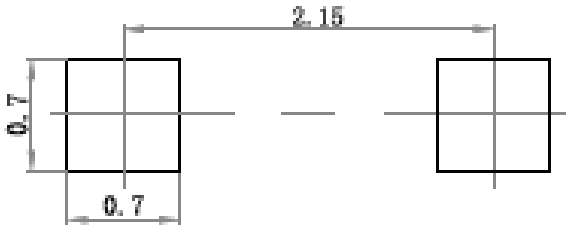
Package Outline Dimensions SOD-323



Pin 1= Cathode
Pin 2 = Anode
Marking bar indicates the cathode.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.